

ABSTRACT**Separation of Semiconductor Devices for Light Emission**

5 A method of fabricating semiconductor devices for light emission is disclosed. The
method comprises providing a substrate with a plurality of epitaxial layers mounted on
the substrate and separating the substrate from the plurality of epitaxial layers while
the plurality of epitaxial layers are intact while preserving electrical and mechanical
10 properties of the plurality of epitaxial layers. Subsequent to separation of the
substrate, a first stage of device isolation is performed by trench etching along edges
of each mesa.

15 **Figure 10**



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